

DYNAMIC CHARACTERISTICS

APT50GN60B_SDQ3(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		3200		pF
C_{oes}	Output Capacitance			125		
C_{res}	Reverse Transfer Capacitance			100		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 50A$		9.0		V
Q_g	Total Gate Charge ^③			325		nC
Q_{ge}	Gate-Emitter Charge			25		
Q_{gc}	Gate-Collector ("Miller") Charge			175		
SSOA	Switching Safe Operating Area	$T_J = 175^\circ\text{C}, R_G = 4.3\Omega^{⑦}, V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 600V$	150			A
SCSOA	Short Circuit Safe Operating Area	$V_{CC} = 360V, V_{GE} = 15V, T_J = 150^\circ\text{C}, R_G = 4.3\Omega^{⑦}$	6			μs
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 4.3\Omega^{⑦}$ $T_J = +25^\circ\text{C}$		20		ns
t_r	Current Rise Time			25		
$t_{d(off)}$	Turn-off Delay Time			230		
t_f	Current Fall Time			100		
E_{on1}	Turn-on Switching Energy ^④			1185		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤			1465		
E_{off}	Turn-off Switching Energy ^⑥			1565		
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 4.3\Omega^{⑦}$ $T_J = +125^\circ\text{C}$		20		ns
t_r	Current Rise Time			25		
$t_{d(off)}$	Turn-off Delay Time			260		
t_f	Current Fall Time			140		
E_{on1}	Turn-on Switching Energy ^④			1205		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤			2078		
E_{off}	Turn-off Switching Energy ^⑥			2125		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.41	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction to Case (DIODE)			.44	
W_T	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

⑦ R_G is external gate resistance, not including $R_{G(int)}$ nor gate driver impedance. (MIC4452)

⑧ Continuous current limited by package lead temperature.

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT50GN60B_SDQ3(G)

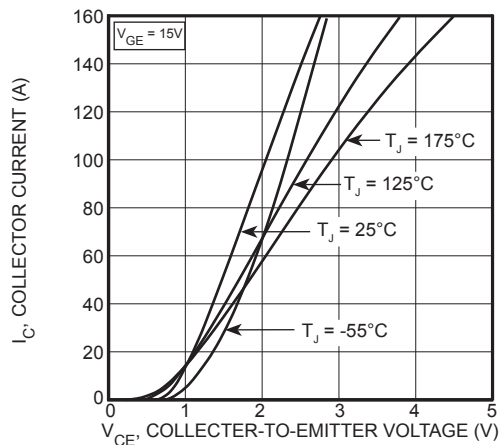


FIGURE 1, Output Characteristics($T_J = 25^{\circ}\text{C}$)

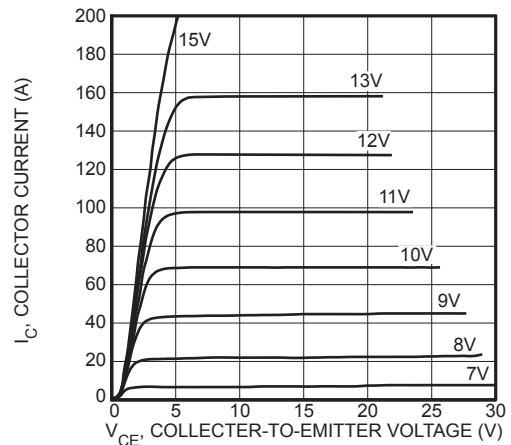


FIGURE 2, Output Characteristics ($T_J = 125^{\circ}\text{C}$)

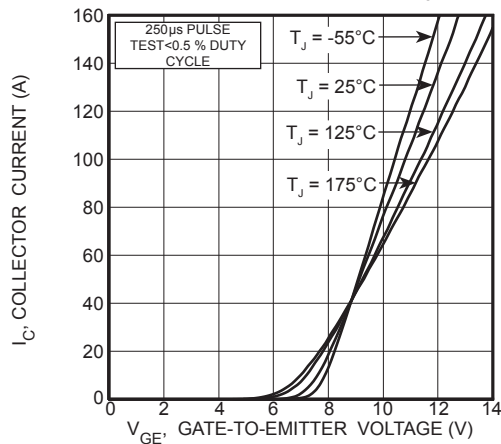


FIGURE 3, Transfer Characteristics

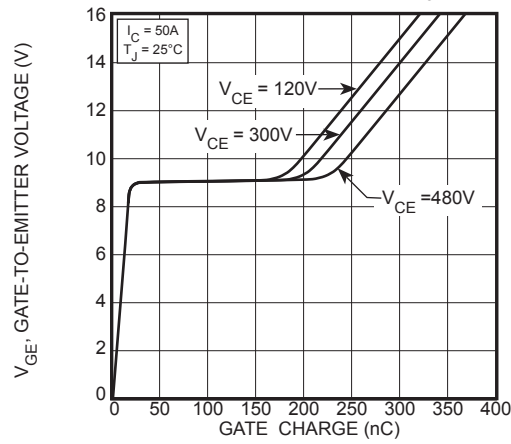


FIGURE 4, Gate Charge

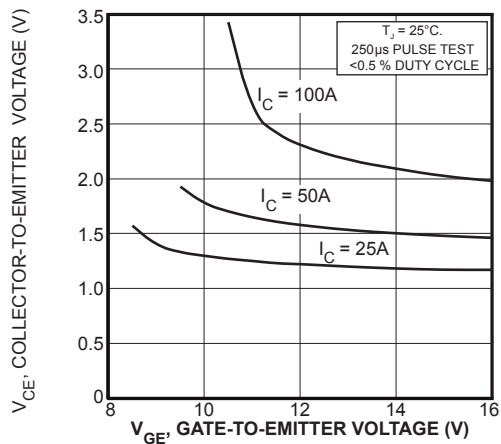


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

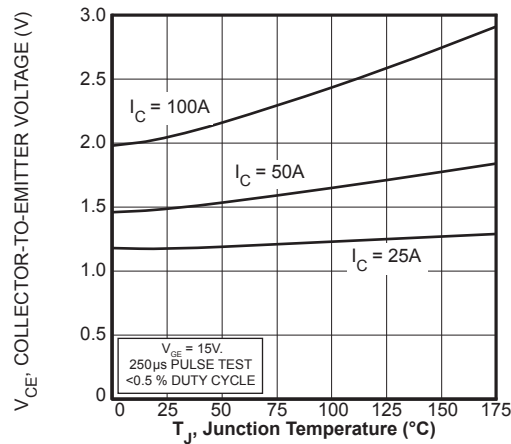


FIGURE 6, On State Voltage vs Junction Temperature

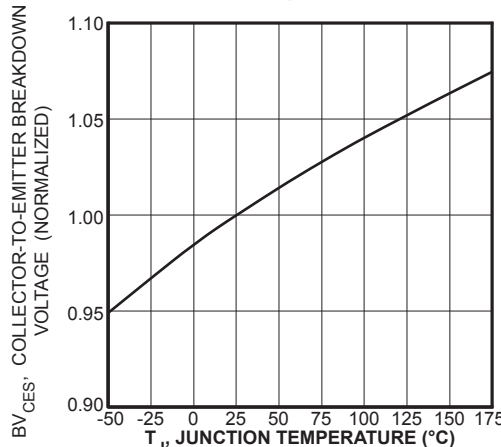


FIGURE 7, Breakdown Voltage vs. Junction Temperature

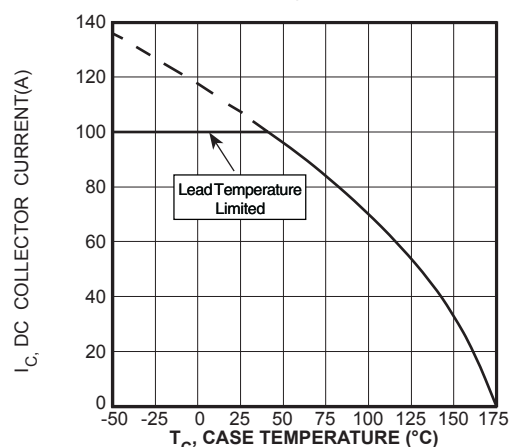


FIGURE 8, DC Collector Current vs Case Temperature

TYPICAL PERFORMANCE CURVES

APT50GN60B_SDQ3(G)

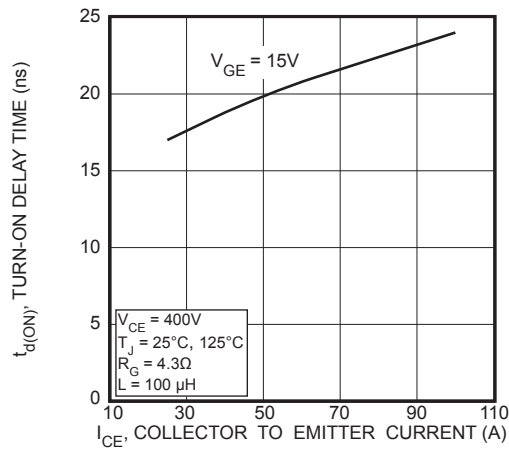


FIGURE 9, Turn-On Delay Time vs Collector Current

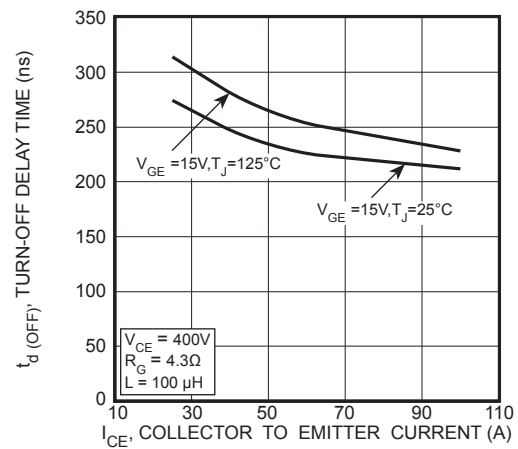


FIGURE 10, Turn-Off Delay Time vs Collector Current

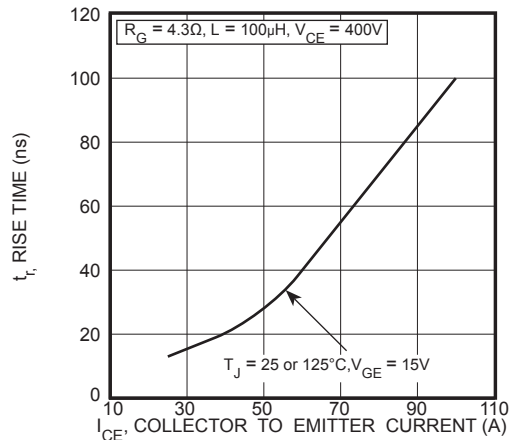


FIGURE 11, Current Rise Time vs Collector Current

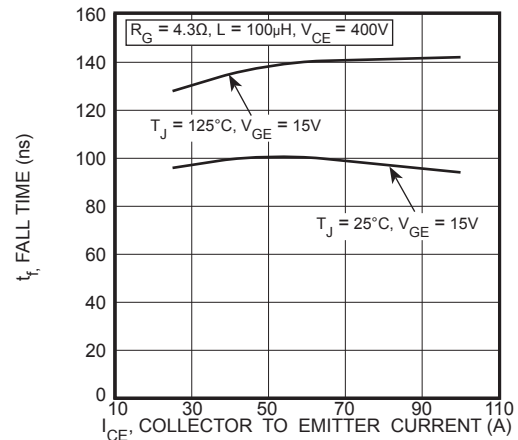


FIGURE 12, Current Fall Time vs Collector Current

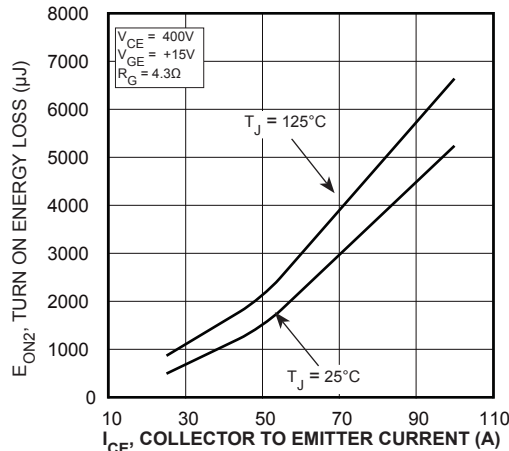


FIGURE 13, Turn-On Energy Loss vs Collector Current

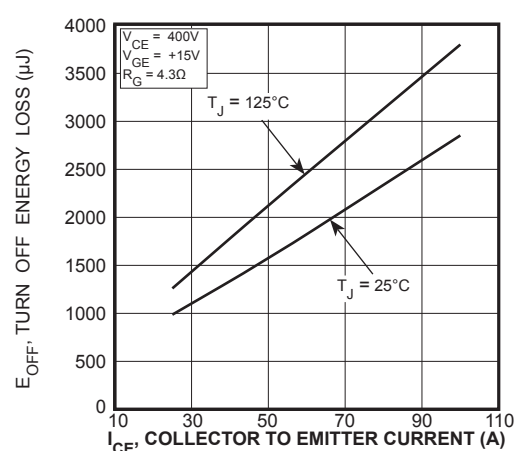


FIGURE 14, Turn Off Energy Loss vs Collector Current

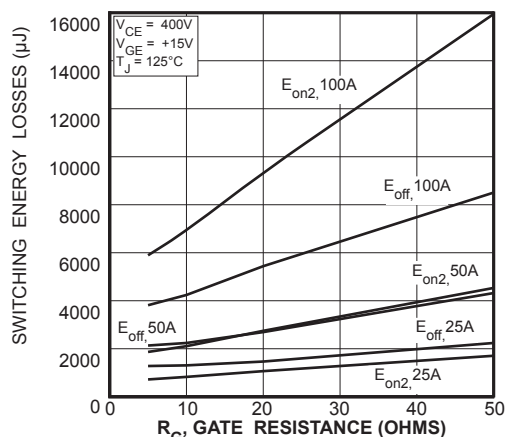


FIGURE 15, Switching Energy Losses vs. Gate Resistance

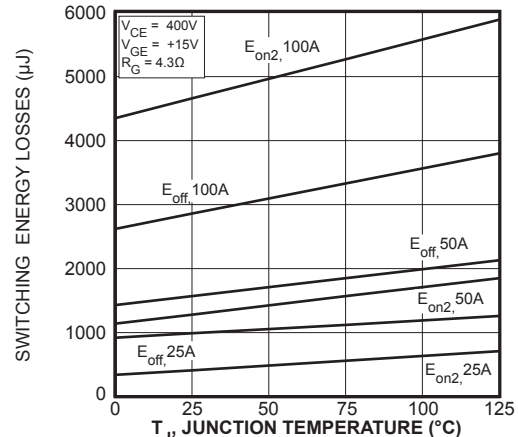


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

APT50GN60B_SDQ3(G)

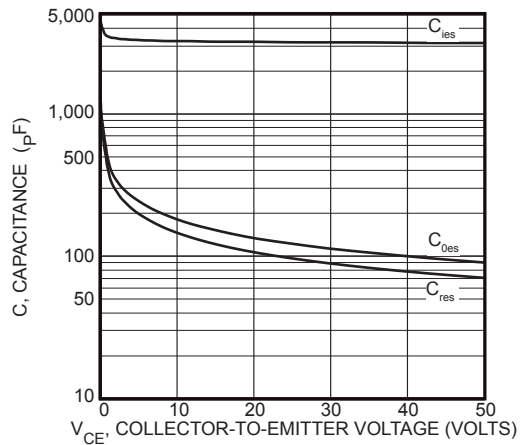


Figure 17, Capacitance vs Collector-To-Emitter Voltage

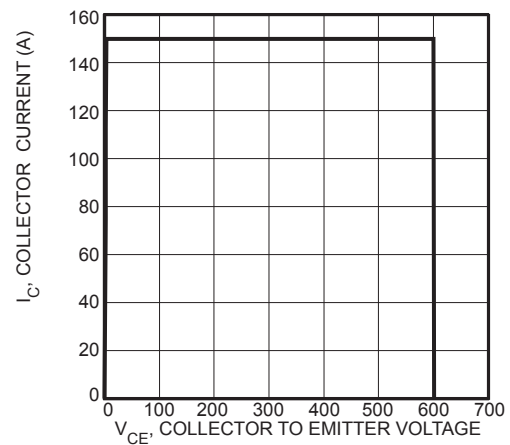


Figure 18, Minimum Switching Safe Operating Area

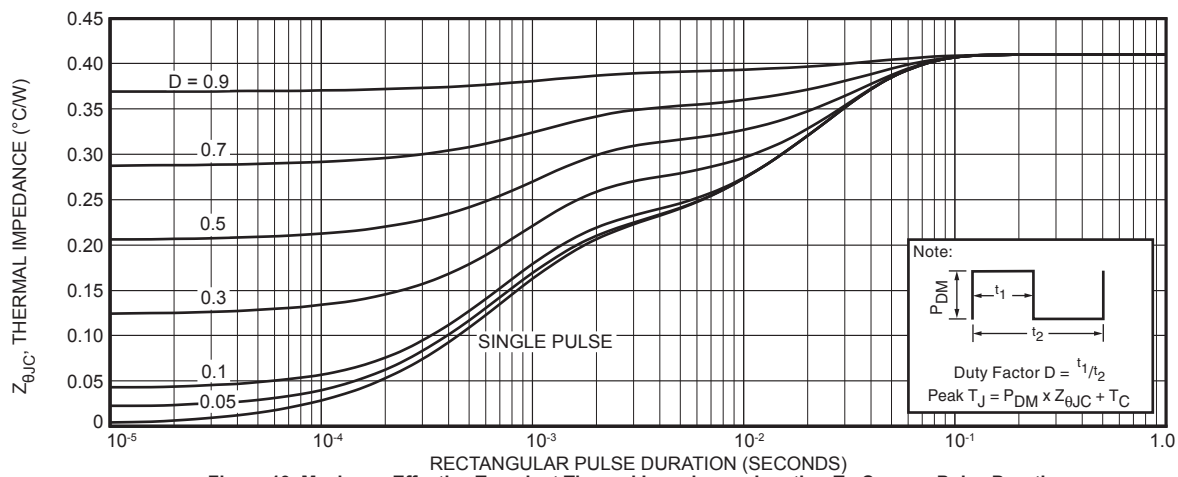


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

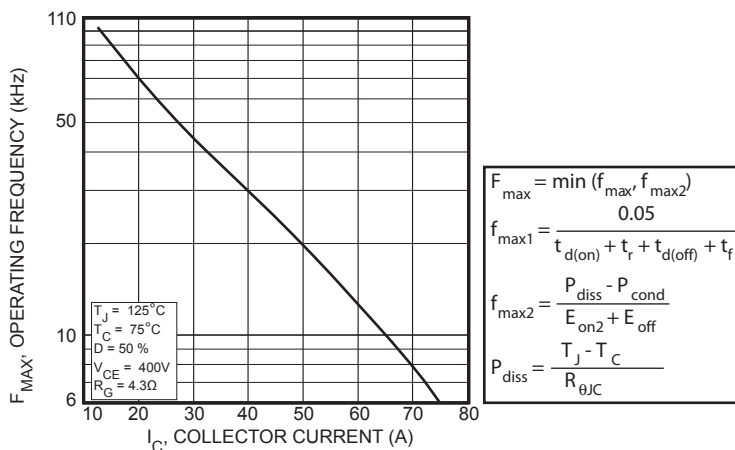
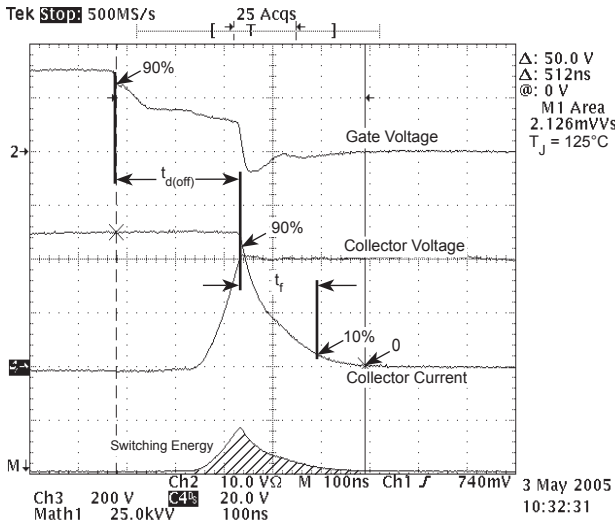
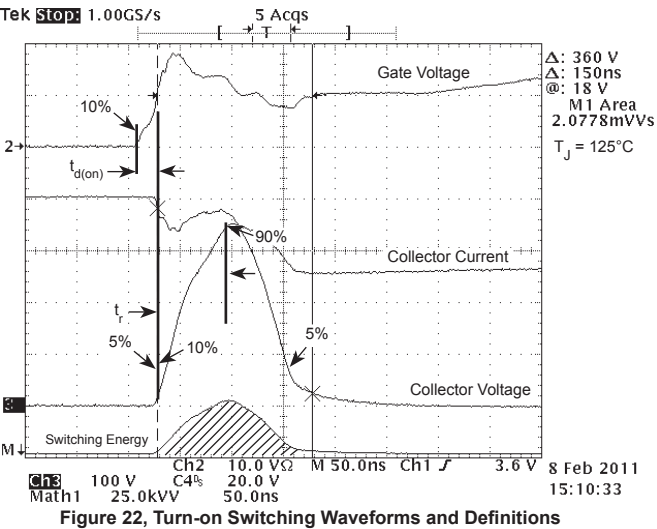
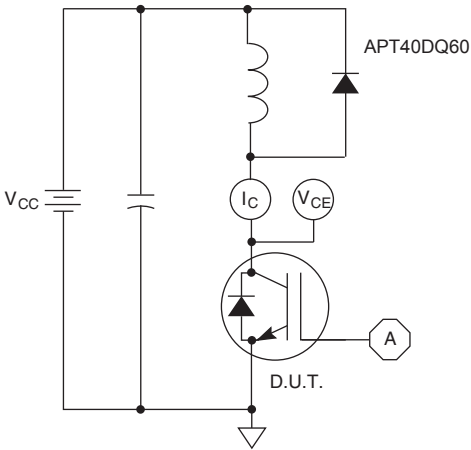


Figure 20, Operating Frequency vs Collector Current



ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT50GN60B_SDQ3(G)			UNIT
$I_{F(AV)}$	Maximum Average Forward Current ($T_C = 110^\circ\text{C}$, Duty Cycle = 0.5)		60		Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)		94		
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)		600		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = 60\text{A}$	2.0		Volts
		$I_F = 120\text{A}$	2.44		
		$I_F = 60\text{A}, T_J = 125^\circ\text{C}$	1.7		

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	26		ns
t_{rr}	Reverse Recovery Time	$I_F = 60\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 25^\circ\text{C}$	-	35		
Q_{rr}	Reverse Recovery Charge		-	45		nC
I_{RRM}	Maximum Reverse Recovery Current		-	4	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 60\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	175		ns
Q_{rr}	Reverse Recovery Charge		-	680		nC
I_{RRM}	Maximum Reverse Recovery Current		-	8	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 60\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	100		ns
Q_{rr}	Reverse Recovery Charge		-	1380		nC
I_{RRM}	Maximum Reverse Recovery Current		-	26		Amps

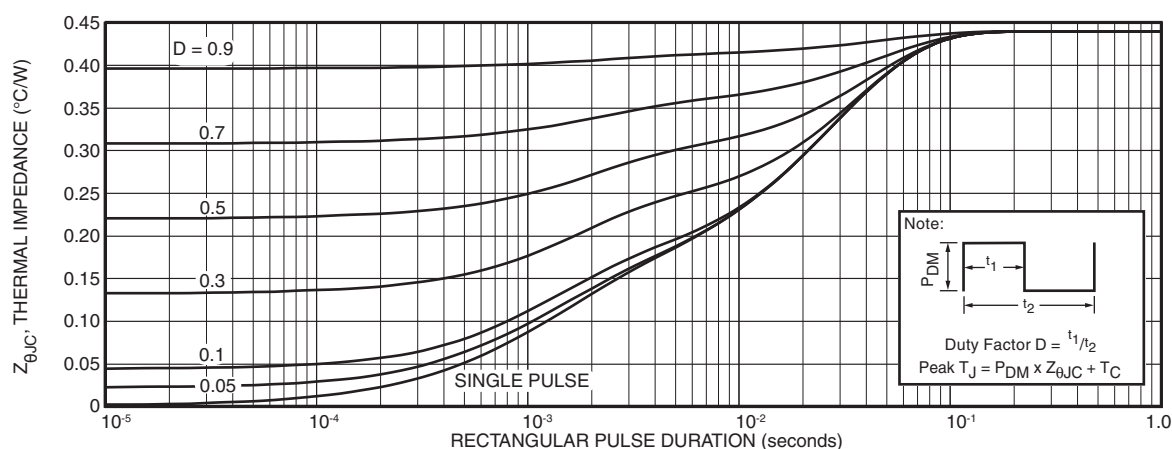


FIGURE 24. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

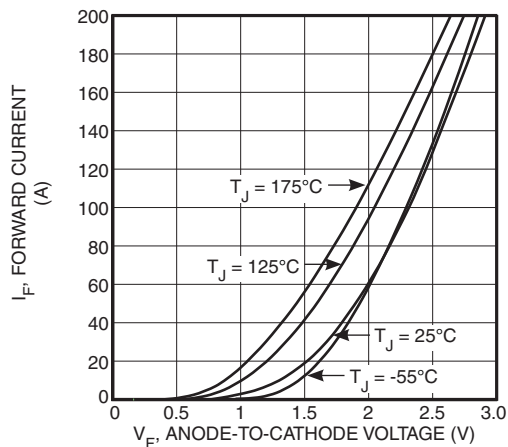


Figure 25. Forward Current vs. Forward Voltage

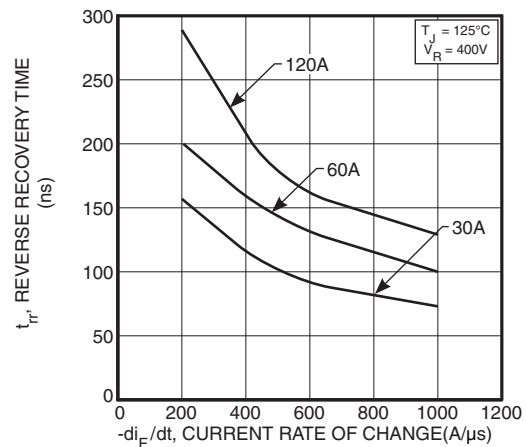


Figure 26. Reverse Recovery Time vs. Current Rate of Change

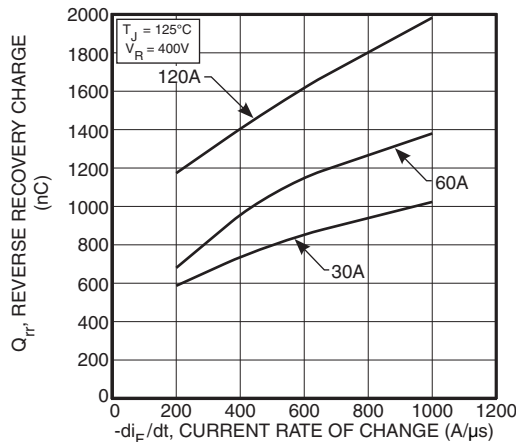


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

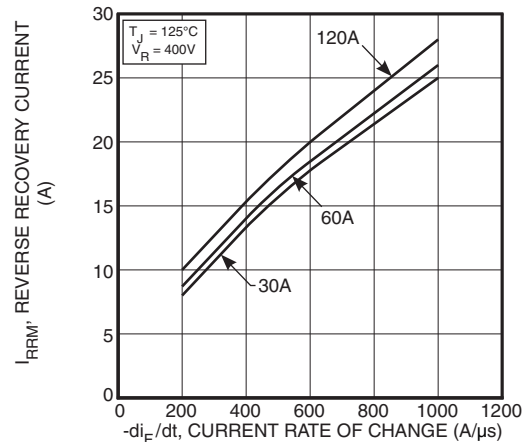


Figure 28. Reverse Recovery Current vs. Current Rate of Change

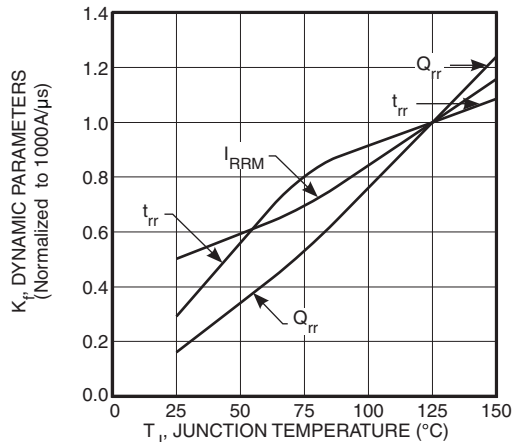


Figure 29. Dynamic Parameters vs. Junction Temperature

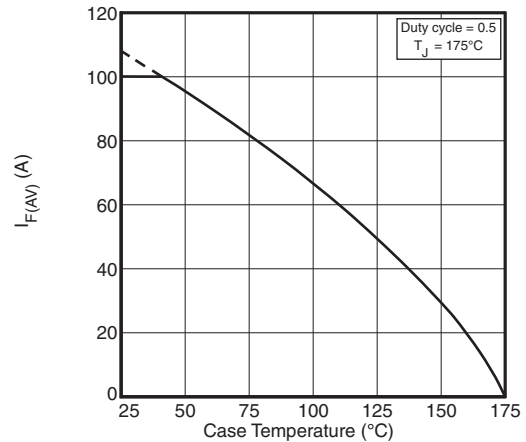


Figure 30. Maximum Average Forward Current vs. Case Temperature

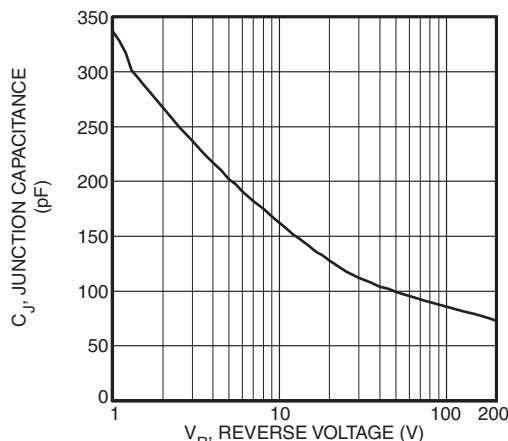


Figure 31. Junction Capacitance vs. Reverse Voltage

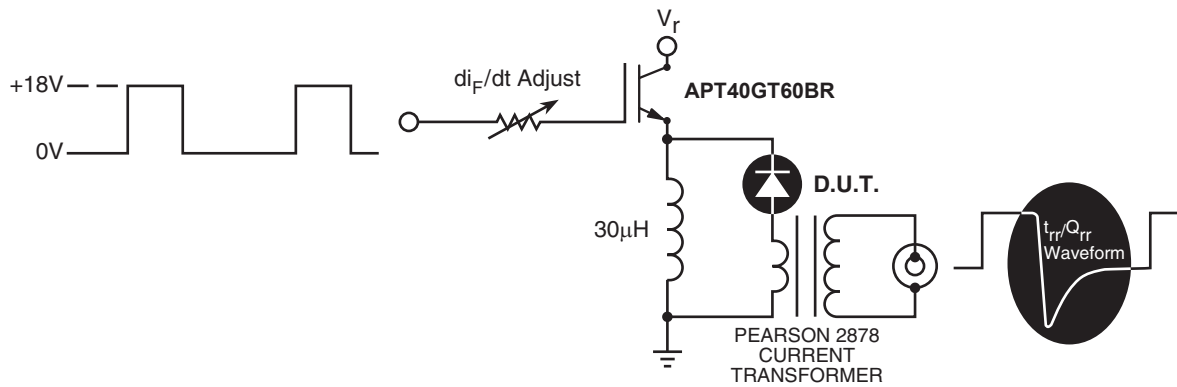


Figure 32. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

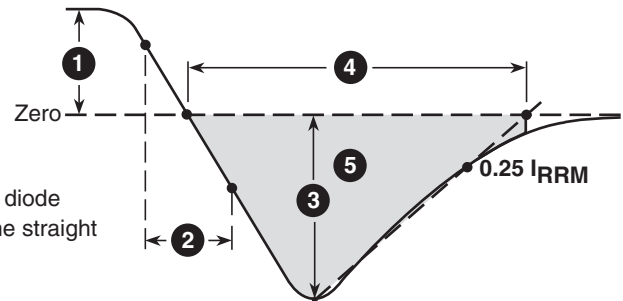
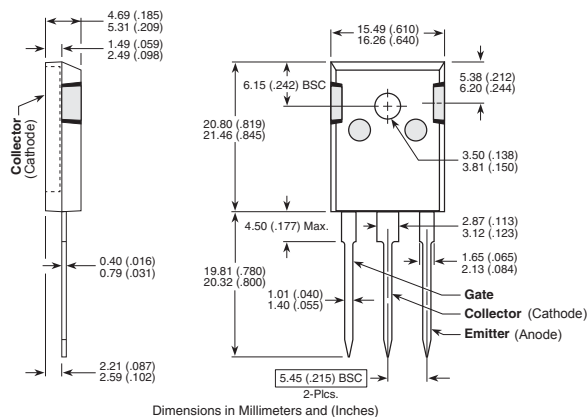


Figure 32, Diode Reverse Recovery Waveform and Definitions

TO-247 Package Outline

② SAC: Tin, Silver, Copper

D³PAK Package Outline

③ 100% Pure Tin

